

Description

The NVMFS5C468N uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = 40V I_D = 50A$ $R_{DS(ON)} < 14m\Omega V_{GS} = 10V$

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

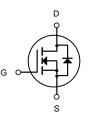
Product ID	Pack	Brand	Qty(PCS)
NVMFS5C468N	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
Vds	Drain-Source Voltage	40	V
Vgs	Gate-Source Voltage	±20	V
l₀@Tc=25°C	Continuous Drain Current, V _{GS} @ 10V ¹	50	А
l₀@Tc=100°C	Continuous Drain Current, Vos @ 10V1	38	А
Ідм	Pulsed Drain Current ²	160	А
EAS	Single Pulse Avalanche Energy ³	50	mJ
Тѕтс	Storage Temperature Range	-55 to 175	°C
TJ	Operating Junction Temperature Range	-55 to 175	°C







N-Channel MOSFET



NVMFS5C468N

N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_c=25[°]C unless otherwise noted)

Parameter	Parameter Symbol Cond		Min	Тур	Max	Unit
Off Characteristics	·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	·			•		
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	11	14	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =20A	30	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss		-	1540	-	PF
Output Capacitance	C _{oss}	$V_{DS}=25V, V_{GS}=0V,$	-	171	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	115	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	5.0	-	nS
Turn-on Rise Time	tr	V _{DD} =20V,I _D =20A,R=1Ω	-	24	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V,R _{GEN} =3 Ω	-	38	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Qg	N/ 00)//L 00A	-	24	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =30V,I _D =30A, V _{GS} =10V	-	5.9	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	3.6	-	nC
Drain-Source Diode Characteristics			ł	1 1		
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =30A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	48	A
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =30A	-	9		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	15		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

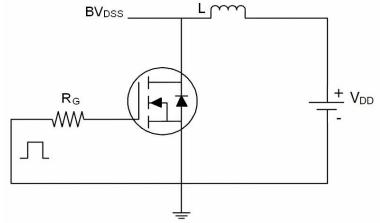
4. Guaranteed by design, not subject to production

5. E_{AS} condition: Tj=25 $^\circ C$,V_{DD}=30V,V_G=10V,L=0.5mH,Rg=25\Omega

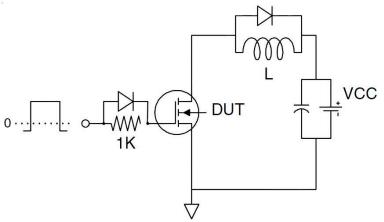


Test circuit

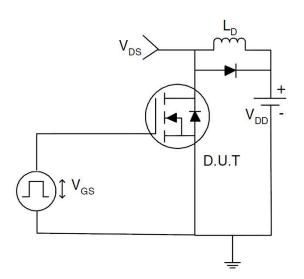
1) E_{AS} test Circuits



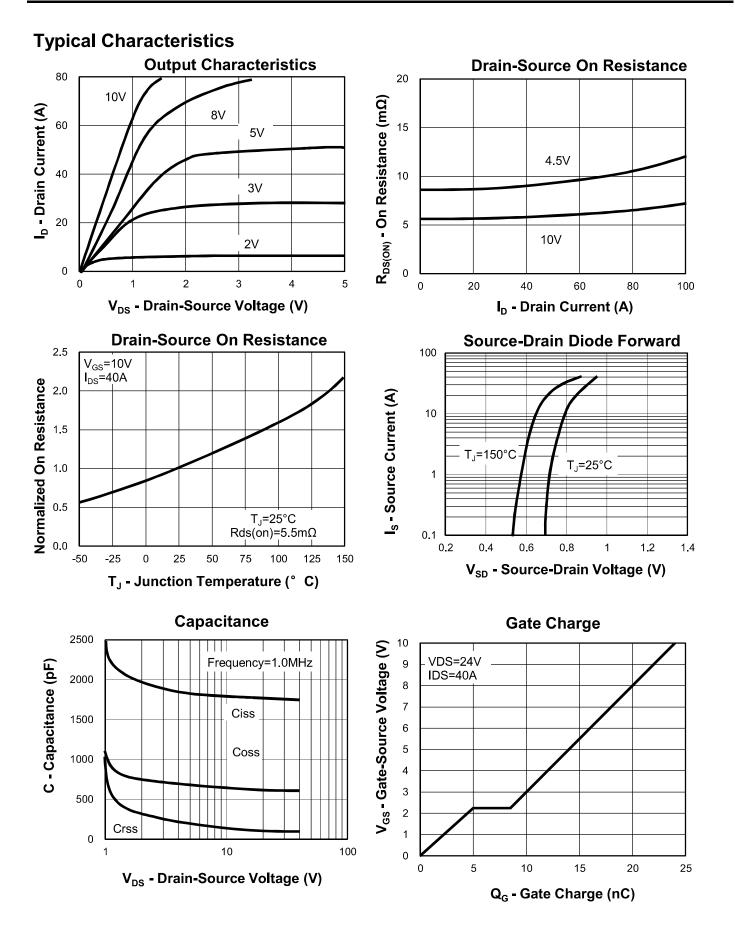
2) Gate charge test Circuit



3) Switch Time Test Circuit

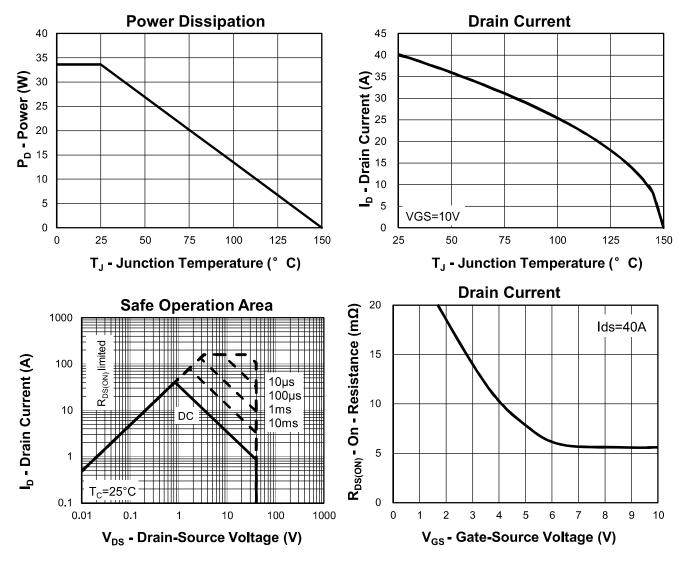




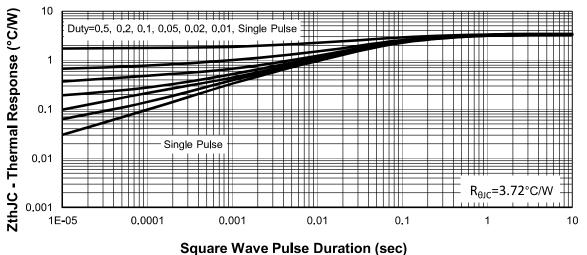




Typical Characteristics

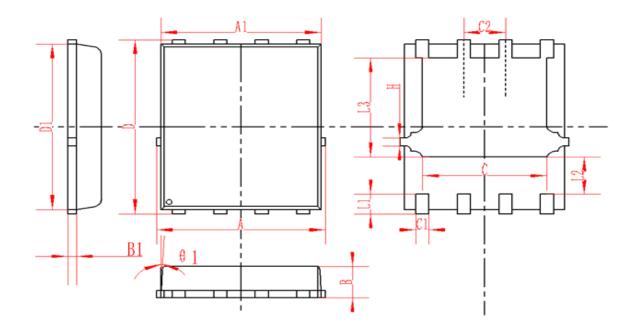








DFN5X6-8L Package Information



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF		0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010



Attention

Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.

• HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.

• Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could

give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

• In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

• No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.

Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production.
HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.